

Thin Film Measurement

Kirk Lau (9713279)

McMaster University, 1280 Main St. W, Hamilton, ON, L8S 4K1, Canada

laukk@mcmaster.ca

Abstract: The most efficient way to measure thickness of a semi-conductor sample and its insulation layer, is to use Fizeau technique and Ellipsometry; Michelson provide more accurate value, but is more complicated.

Introduction:

As semi-conductor technologies getting more and more advance everyday, the thickness the integrated circuit masking are getting thinner and thinner. And the thickness of the thin film is crucial. Therefore, an accurate measurement is required. Consider the thickness of the masking is in atom-size scale, normal mechanical measurement will never be able to provide a value. Consequently, optical measurements are being use.

In this experiment, one had tested several method of thin film thickness measuring. These methods included using Michelson Technique, Fizeau Technique, and Ellipsometry technique.

Methods and Theories:

Three different techniques had been used in this laboratory, Michelson, Fizeau, and Ellipsometry. For Michelson and Fizeau, Light interference was being used; for Ellipsometry, Polarization was being used.

In 1887, Albert Michelson and Edward Morley had built an interferometer in order to detect the earth's motion through the ether optically (Pedrotti, 3). However, it turns out that this device can be very useful in measurement of atom scale objects.

The setup in this laboratory, the Michelson interferometer was setup as follow (fig 1):

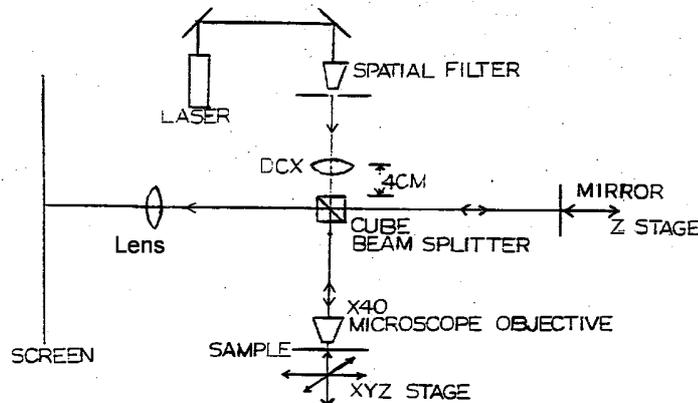


Fig 1: Lab Setup for Michelson interferometer (Lab, 2)

[Modified with extra lens before screen]

If the microscope objective and if the samples is replaced by a mirror, then an interference pattern will appear on the screen (Fig. 2) once the path difference between the two reflected beam equal zero (Pedrotti 227). However, due to the fact that the sample consists of masking that have a very small, but finite thickness. There should be a small path difference between the mask and the base of the sample. As a result, the interference pattern will have a step when the edge of the mask is being project to the screen.

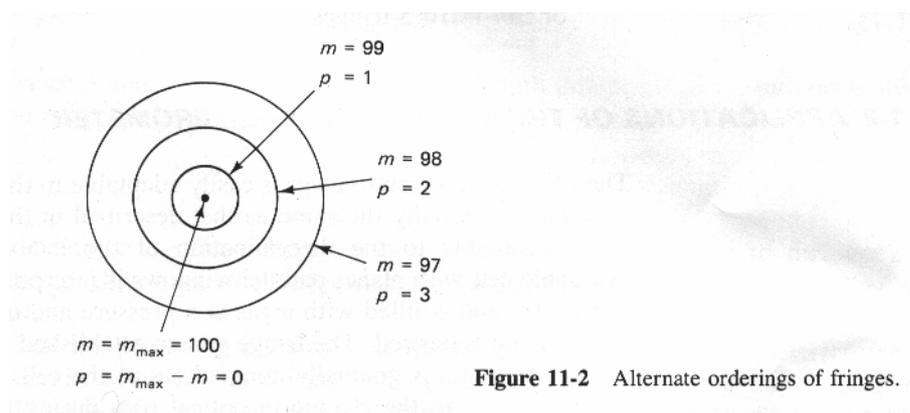


Figure 11-2 Alternate orderings of fringes.

Fig 2: Interference pattern expected to see on the screen. (Pedrotti, 227)

The finite thickness of the thin film will create a path difference to the light. And therefore one can first the base to be zero path length, then measure how much does it require to move backward to get zero path length for the film. Then the change will be proportional to the thickness. The thickness and the change in position is proportional the magnification and the refractive index of oxide on the sample, which is equal to 1.46.

$$thickness = \frac{change_in_micrometer_position}{magnification \times \eta_{oxide}}$$

Equation 1: Equation used in Michelson technique (Lab, 2)

Fizeau fringes were usually appeared in air wedge. It appears due to the reflection of two or more surfaces interfere with each other. However, whenever there is a small step on the masking, it will display on the screen as well. With this technique, the thickness of the mask, or depth of a defect can be measure. The technique was widely used in the industries to measure the thickness of substrate.

The basic idea of setup of the Fizeau technique is shown in fig 3. Since the thickness of the mask had introduced a small path difference, a small bump will appear along with the interference pattern. The expected pattern should be similar to fig 4.

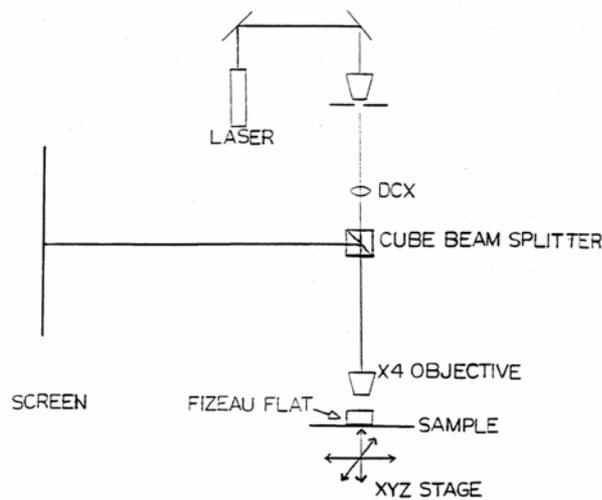


Fig 3, Setup for Fizeau technique of thickness measuring (Lab, 3)

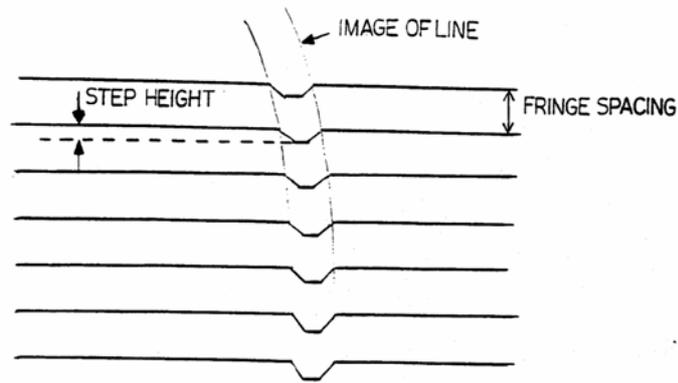


Fig 4: Expected pattern in Fizeau measurement technique (Lab, 4)

$$Film_Thickness = 3164 \times \frac{Step_height}{Fringe_spacing}$$

Equation 2: Equation to be used in Fizeau interference measurement technique (Lab, 4)

Metal oxide is usually grown on top of the circuits in order to provide insulation. The thickness of the oxide is very essential; however, one would also like to ignore the integrated circuit structure itself. This could be done by using an ellipsometer (Lab, 5).

The setup of the Ellipsometry is shown in figure 5. A mercury green line of 546.07nm was being use as the light source. After the polarized light passed through the compensator (birefringent plate), light will be converted to elliptically polarized. However, after the light reflected off the sample oxide layer, it will become linear polarized again. Moreover, the polarization axis can be determine by rotating the analyser (another linear polarizer), maximum intensity will occur when the analyser transmission axis is parallel to the polarization of the light (Lab 6-7)

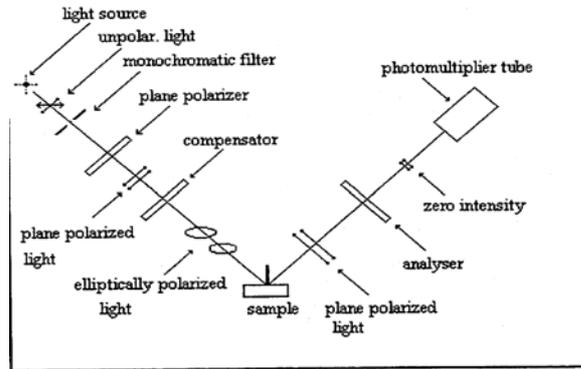


Fig 5: Setup of the ellipsometer (Lab, 7)

The calculation of δ (defined below) can be complicated, and therefore, a table of value was being used (refer to appendix A), given that Δ , ϕ , angle of incidence, refractive indices of the substrate and wavelength is known. (Lab, 7-10)

$$\delta = \left(\frac{360}{\lambda}\right)d(n_1^2 - \sin^2 \phi)^{1/2}$$

$$\Rightarrow d = \delta\left(\frac{\lambda}{360}\right)(n_1^2 - \sin^2 \phi)^{-1/2}$$

Equation 3: Definition of δ (Lab, 9)

$$\Delta = \frac{\pi}{2} - 2P$$

$$\Psi = -A_p = A_s$$

Equations 4: Definitions of Delta and Psi (Lab 7)

Experimental Results:

In terms of Michelson technique, the experiment was not successful. An interference pattern was observed, however, one was not able to measure the change in path length due to the limitation of the equipment. Detail will be explained in discussions part.

On the other hand, by using the Fizeau technique, a result as expected in theory was observed. A picture of the pattern was taken in the lab (Fig. 6), the step height was found to be 28 pixels, and the fringe spacing was found to be 45 pixels.

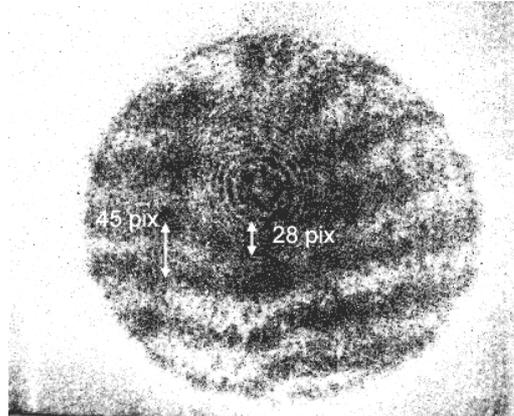


Fig 6: Interference pattern observed using Fizeau technique.

With equation 2 above, the film thickness was found to be 196.8nm.

In term of Ellipsometry, the data were collected and tabulated as follow:

	Sample #1	Sample #3	Sample X
Index of refraction	1.47	1.8	1.6
Compensator Angle	315 °	315°	315°
Polarizer Angle	0°	0°	0°
Analyser Angle	132±2°	330±2°	318±2°
Angle of incidence	69°	69°	69°
Small Delta (From table)	107-140°	130-140°	113-140°
Thickness(from Equation 3)	142.9-187.0nm	128.1-138.0nm	131.9-163.4nm

Table 1: Experimental result for Ellipsometry

With equations 4 above, the Capital Delta is found to be $1/2\pi$, $\Psi= 132^\circ$ and 350° for sample 1 and 3 respectively. According to the table of small delta and equation 3, one can easily found the thickness of the oxide. The values are shown in table 1.

Discussions:

The failure of the Michelson technique in this laboratory is due to the limitation of the equipment. In this experiment, the path length was changed by a micrometer; however, the smallest scale on the micrometer is 1/100mm. On the other hand, the thickness is in the order of hundreds of angstrom. As one can see, the measurement is much smaller than the scale the equipment can be measure. As a result, measurement cannot be made (3W04). However, if limitation of equipment were allowed, a precise measurement could be made.

Comparing between the Michelson and Fizeau techniques, the advantage of Michelson its it provide a more accurate measurement, since there are no measurement of the pattern were involve. While the Fizeau technique is rather hard to justify where the maximum and minimum of are each fringes located.

However, on the other hand, the Fizeau technique is much easier to setup. Because the sample in Michelson was magnified 40 times, a small movement or misalignment will destroy the interference pattern. Moreover, the Fizeau does not require adjustment to achieve zero path length. Where in Michelson case requires a long time to find effective zero paths difference (since the objective will introduce an extra distance due to higher refractive index).

For Ellipsometry, it is used for measuring the thickness of the oxide layer on top of the circuit. Due to the complicity of the equations, a table was used. Since it is impossible to include all the value in a table, accuracy had decreased. After one simplified the equations, it will end up with an equation with different unknown in the exponential function (Appendix B). The only way to solve it is by trial and error, by comparing the value in the exponential, and that can be easily done with computer. With computer, using Newton method (Mathews & Fink, 70-80), an accurate answer can be found.

With the use of table or computer, thickness of the oxide can be calculated very easily with Ellipsometry.

Conclusions:

In conclusion, the Michelson method is the most complicated to setup, however, it provide more accurate value of calculations. The most efficient way to gather information of a semi-conductor is to use Fizeau technique to measure the thickness circuit and use Ellipsometry to measure the thickness of the oxide.

Work Cited

3W04, Dr. D. Cassidy, Course notes.

Lab Manual, Engineering Physics 4U04

Pedrotti, F and Pedrotti, L. Introduction to Optics, Prentice-Hall Inc. New Jersey, 1993

Mathews, J and Fink, K. Numerical Methods using MATLAB. Prentice-Hall Inc.

Upper Saddle River, 1992

Appendix B: Sample calculations and derivations

Sample calculation and table lookup for Sample 3 in Ellipsometry method:

For $A_s = 330^\circ$, Compensator = $-\pi/4$

According to table below, $P = P + \pi/2 = \pi/2$, and $A = 2\pi - A_s = 30^\circ$

ZONES	COMPENSATOR	P	A
1	$-\pi/4$	P	A_p
		$P + \pi$	A_p
		P	$AP + \pi$
		$P + \pi$	$AP + \pi$
2	$+\pi/4$	$\pi/2 - P$	A_s
		$3\pi/2 - P$	A_s
		$\pi/2 - P$	$A_s + \pi$
		$3\pi/2 - P$	$A_s + \pi$
3	$-\pi/4$	$P + \pi/2$	$\pi - A_s$
		$P + 3\pi/2$	$\pi - A_s$
		$P + \pi/2$	$2\pi - A_s$
		$P + 3\pi/2$	$2\pi - A_s$
4	$+\pi/4$	$\pi - P$	$\pi - A_p$
		$2\pi - P$	$\pi - A_p$
		$\pi - P$	$2\pi - A_p$
		$2\pi - P$	$2\pi - A_p$

Table b: Relationship between Compensator, P and A (Lab, 8)

Applied P and A to Equation 4,

$$\Delta = \frac{\pi}{2} - 2P = \frac{-\pi}{2}$$

$$\Psi = -A_p = A_s = 30^\circ$$

Look up in Appendix A, one would find the value for small delta from above values is approximately equal to 130°

Then apply small delta to equation 3 to find the thickness, d.

Derivation of formula to solve for thickness in Ellipsometry:

From the Fresnel reflection coefficients, one has:

$$\tan \Psi e^{i\Delta} = \frac{r_{p01} + r_{p12} e^{-2i\delta}}{1 + r_{p01} r_{p12} e^{-2i\delta}} \times \frac{1 + r_{s01} r_{s12} e^{-2i\delta}}{r_{s01} + r_{s12} e^{-2i\delta}} \quad (\text{Lab, 9})$$

Expand the above, one will get

$$\tan \Psi e^{i\Delta} = \frac{r_{p01} + r_{p12} e^{-2i\delta} + r_{s01} r_{s12} r_{p01} e^{-2i\delta} + r_{s01} r_{s12} r_{p12} e^{-4i\delta}}{r_{s01} + r_{s12} e^{-2i\delta} + r_{s01} r_{p12} r_{p01} e^{-2i\delta} + r_{p01} r_{s12} r_{p12} e^{-4i\delta}}$$

Where r's are given by Fresnel Reflection equations:

$$\begin{aligned} r_{pab} &= (n_a \cos \phi_2 - n_b \cos \phi_1) / (n_a \cos \phi_2 + n_b \cos \phi_1) \\ r_{sab} &= (n_a \cos \phi_1 - n_b \cos \phi_2) / (n_a \cos \phi_1 + n_b \cos \phi_2) \end{aligned} \quad (\text{Lab, 9})$$

Once all the measured values had been substitute in the equations above, only unknown left over is small delta, and one can use trial and error method to find the value, with use of computer and Newton Root Finding Method.

Derivation of formula in Michelson experiment:

At zero path length difference, Effective Path length between mirror and cube (PLM) and effective Path length different between sample and Cube (PLS) are equal.

Therefore:

$$\begin{aligned} PLA &= PLM + \left(\frac{n_{oxide}}{n_{air}}\right)d \\ \Rightarrow PLA - PLM &= \left(\frac{n_{oxide}}{n_{air}}\right)d = \frac{D_{micrometer}}{\text{Magnification}} \\ \ominus n_{air} &\cong 1 \\ \Rightarrow \text{thickness} &= \frac{\text{change in Position}}{\text{Magnification} \times n_{oxide}} \end{aligned}$$

The magnification factor is introduce due to the microscope objective is enlarging the effective thickness of the sample.